MITSUBISHI RF POWER TRANSISTOR

2SC2237

NPN EPITAXIAL PLANAR TYPE

DESCRIPTION

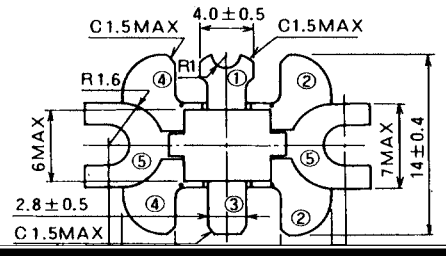
2SC2237 is a silicon NPN epitaxial planar type transistor designed for RF power amplifiers in VHF band mobile radio applications.

FEATURES

- High power gain: $G_{pe} \geqq 13.8$dB
  @V_{CC} = 13.5V, P_O = 6W, f = 175MHz
- Emitter ballasted construction and gold metallization for high reliability and good performances.
- Low thermal resistance ceramic package with flange.
- Ability of withstanding more than 20:1 load VSWR when

OUTLINE DRAWING

Dimensions in mm



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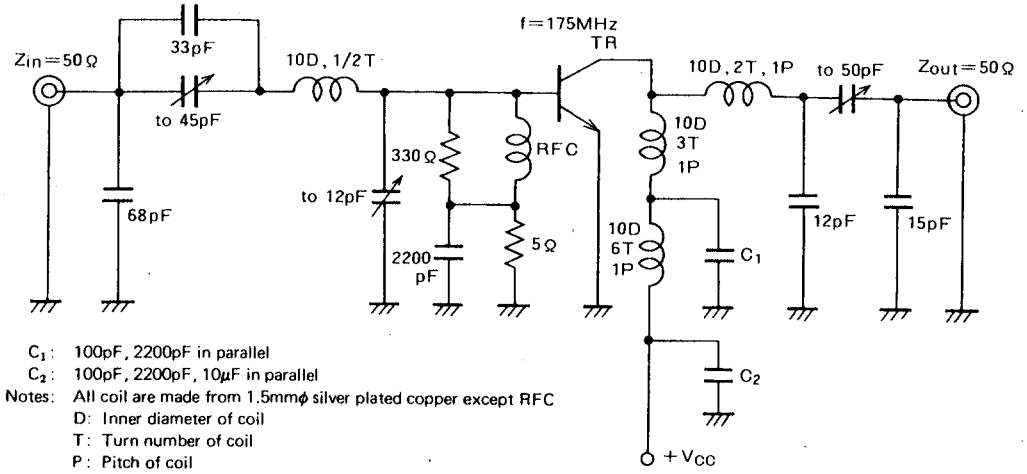
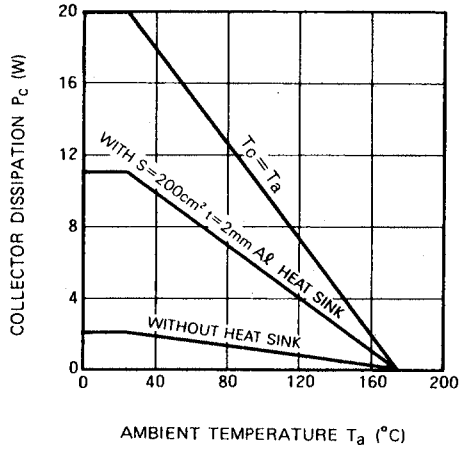
TEST CIRCUIT



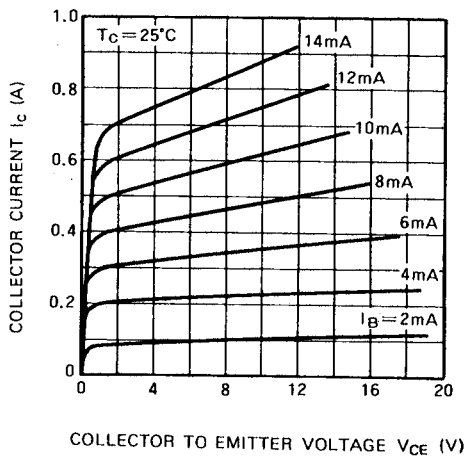
C_1: 100pF, 2200pF in parallel
C_2: 100pF, 2200pF, 10μF in parallel
Notes: All coil are made from 1.5mmϕ silver plated copper except RFC
D: Inner diameter of coil
T: Turn number of coil
P: Pitch of coil
Dimension in milli-meter

TYPICAL PERFORMANCE DATA

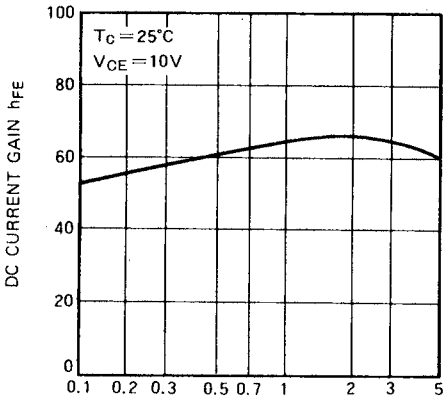
COLLECTOR DISSIPATION VS. AMBIENT TEMPERATURE



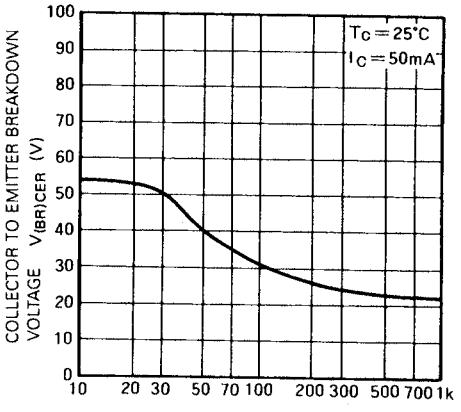
COLLECTOR CURRENT VS. COLLECTOR TO EMITTER VOLTAGE



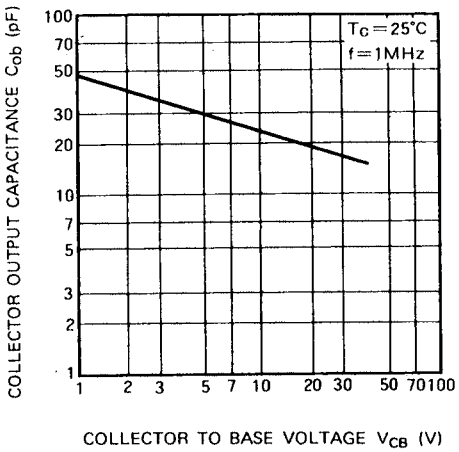
DC CURRENT GAIN VS. COLLECTOR CURRENT



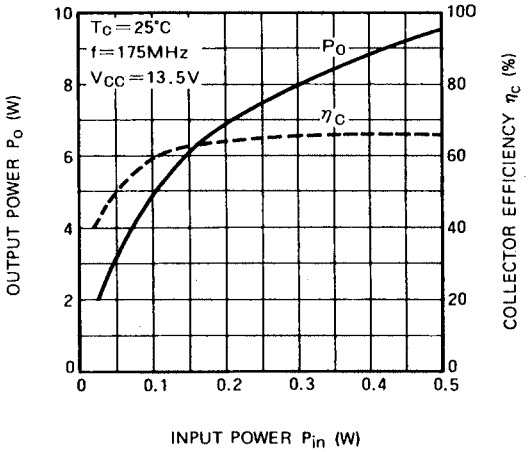
COLLECTOR TO EMITTER BREAKDOWN VOLTAGE VS. BASE TO EMITTER RESISTANCE



COLLECTOR OUTPUT CAPACITANCE VS. COLLECTOR TO BASE VOLTAGE



OUTPUT POWER, COLLECTOR EFFICIENCY VS. INPUT POWER



OUTPUT POWER VS. COLLECTOR SUPPLY VOLTAGE